

WaferWave Technologies | Product Specification

100mm Prime Grade Silicon Wafer (CZ, P-Type, <100>)

Product Overview:

This high-purity Prime Grade substrate is engineered for advanced semiconductor fabrication, high-resolution lithography, and MEMS applications. Featuring an elite Total Thickness Variation (TTV) of <5 µm and ultra-low particle counts, this wafer ensures maximum yield for front-end-of-line (FEOL) processes.

1. Physical & Crystallographic Properties

Specification	Value
Diameter	100 ± 0.3 mm
Material	Silicon (Si)
Growth Method	Czochralski (CZ)
Grade	Prime (Device Quality)
Type / Dopant	P-Type / Boron (P/B)
Crystal Orientation	<100> ± 0.5°
Resistivity	1.0 – 5.0 Ω-cm

2. Mechanical Specifications

Specification	Value
Thickness	525 ± 20 µm

Total Thickness Variation (TTV)	< 5 μm
Bow	< 30 μm
Warp	< 30 μm
Orientation Features	2 SEMI-Standard Flats
Primary Flat Location	@ {110} $\pm 1^\circ$
Primary Flat Length	32.5 \pm 2.5 mm
Secondary Flat Location	90° CW from Primary Flat
Secondary Flat Length	18.0 \pm 2.0 mm

3. Surface & Purity Control

Specification	Value
Surface Finish (Front)	Mirror Polished (SSP)
Surface Finish (Back)	Etched / Standard Finish
Particle Count	< 10 ea/wf (@ $\geq 0.3 \mu\text{m}$)
Laser Mark	None

4. Packaging & Documentation

Specification	Value
Packaging	25-Slot Polypropylene Cassette (Standard Wafer Jar)
Sealing	Double-bagged, Vacuum-sealed, ESD-protected

Compliance

Full Certificate of Analysis (COA) / Conformance (COC) included

Contact Information:

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